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Der Präsident des Europäischen Patentamts;
Im Auftrag

For the President of the European Patent Office

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Self-aligned process for manufacturing a phase change memory cell and phase
change memory cell thereby manufactured

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SELF-ALIGNED PROCESS FOR MANUFACTURING A PHASE CHANGE MEMORY CELL AND PHASE CHANGE MEMORY CELL THEREBY MANUFACTURED

5 The present invention relates to a self-aligned process for manufacturing a phase change memory cell and to a phase change memory cell thereby manufactured.

10 As is known, phase change memory (PCM) elements exploit the characteristics of materials which have the property of changing between two phases having distinct electrical characteristics. For example, these materials may change from an amorphous phase, which is disordered, to a crystalline or polycrystalline phase, which is ordered, and the two phases are associated to considerably different resistivities.

15 At present, alloys of group VI of the periodic table, such as Te or Se, referred to as chalcogenides or chalcogenic materials, can advantageously be used in phase change cells. The chalcogenide that currently offers the best promises is
20 formed by a Ge, Sb and Te alloy ($\text{Ge}_2\text{Sb}_2\text{Te}_5$) and is widely used for storing information in overwritable disks.

25 In chalcogenides, the resistivity varies by two or more magnitude orders when the material passes from the amorphous phase (more resistive) to the polycrystalline phase (more conductive) and vice versa. The characteristics of chalcogenides in the two phases are shown in Figure 1. As may be noted, at a given read voltage, here designated by V_r , there is a resistance variation of more than 10.

30 Phase change may be obtained by locally increasing the temperature, as shown in Figure 2. Below 150°C both phases are stable. Above 200°C (temperature of start of nucleation, designated by T_x), fast nucleation of the crystallites takes
35 place, and, if the material is kept at the crystallization temperature for a sufficient length of time (time t_2), it changes its phase and becomes crystalline. To bring the chalcogenide back into the amorphous state, it is necessary to

raise the temperature above the melting temperature T_m (approximately 600°C) and then to cool the chalcogenide off rapidly (time t_1).

5 From the electrical standpoint, it is possible to reach both critical temperatures, namely the crystallization temperature and the melting point, by causing a current to flow through a resistive element which heats the chalcogenic material by the Joule effect.

10

The basic structure of a PCM element 1 which operates according to the principles described above is shown in Figure 3 and comprises a resistive element 2 (heater) and a programmable element 3. The programmable element 3 is made of
15 a chalcogenide and is normally in the polycrystalline state in order to enable a good flow of current. One part of the programmable element 3 is in direct contact with the resistive element 2 and forms the area affected by phase change, hereinafter referred to as the phase change portion 4.

20

If an electric current having an appropriate value is caused to pass through the resistive element 2, it is possible to heat the phase change portion 4 selectively up to the crystallization temperature or to the melting temperature and
25 to cause phase change. In particular, if a current I flows through a resistive element 2 having resistance R , the heat generated is equal to I^2R .

The use of the PCM element of Figure 3 for forming memory
30 cells has already been proposed. In order to prevent noise caused by adjacent memory cells, the PCM element is generally associated to a selection element, such a MOS transistor, a bipolar transistor, or a diode.

35 All the known approaches are, however, disadvantageous due to the difficulty in finding solutions that meet present requirements as regards capacity for withstanding the

operating currents and voltages, as well as functionality and compatibility with present CMOS technologies.

5 In particular, considerations of a technological and electrical nature impose the creation of a contact area of small dimensions, preferably 20 nm x 20 nm, between the chalcogenic region and a resistive element. However, these dimensions are much smaller than those that can be obtained with current optical (UV) lithographic techniques, which
10 scarcely reach 100 linear nm.

To solve the above problem, patent application 01128461.9, filed on 5.12.2001, and entitled "Small area contact region, high efficiency phase change memory cell, and manufacturing
15 method thereof", teaches forming the contact area as an intersection of two thin portions extending transversely with respect to one another and each of a sublithographic size. In order to form the thin portions, deposition of layers is adopted instead of a lithographic process, given that
20 deposition makes it possible to obtain very thin layers, i.e., having a thickness much smaller than the current minimum size that can be achieved using lithographic techniques.

For a better understanding of the problem of the present
25 invention, the manufacturing process object of the above mentioned patent application No. 01128461.9 will now be described.

With reference to Figure 4, initially a wafer 10 comprising a
30 P-type substrate 11 is subjected to standard front end steps. In particular, inside the substrate 11 insulation regions 12 are formed and delimit active areas 16; then N-type base regions 13 are implanted.

35 Next, a first dielectric layer 18 is deposited and planarized; openings are formed in the first dielectric layer 18 above the base regions 13. At this point, using two dedicated masks and exploiting the self-alignment in the openings, N⁺-type base

contact regions 14 and P⁺-type emitter regions 15 are implanted. Then the openings in the first dielectric layer 18 are covered by a barrier layer, for example a Ti/TiN layer, before being filled with tungsten to form base contacts 19b and emitter contacts 19a. The base contacts 19b are thus in electrical contact with the base regions 13, and the emitter contacts 19a are in direct electrical contact with the emitter regions 15. In this way, the structure of Figure 4 is obtained. The base regions 13, base contact regions 14, and emitter regions 15 form diodes that form selection elements for the memory cells.

Figure 5 shows the layout of some masks used for forming the structure of Figure 4 regarding a pair of memory cells 5 that are adjacent in a perpendicular direction to the sectional plane of Figure 4 (Y direction). In particular, the figure shows a mask A used for defining the active areas 16, a mask B used for implanting the emitter regions 15, and a mask C for forming the openings where the base contacts 19b and the emitter contacts 19a are to be formed. Figure 4 is a cross-section taken along line IV-IV of Figure 5, while Figure 6 shows the same structure sectioned along the section line VI-VI of Figure 5.

Next (Figure 7), a second dielectric layer 20 -for example, an undoped silicon glass (USG) layer- is deposited, and openings 21 are formed in the second dielectric layer 20 above the emitter contact 19a. The openings 21 have dimensions dictated by the lithographic process and are, for example, circle-shaped. Next, a heating layer, for example of TiSiN, TiAlN or TiSiC, is deposited for a thickness of 10-50 nm, preferably 20 nm. The heating layer, designed to form the resistive element 2 of Figure 3, conformally coats the walls and bottom of the openings 21. The openings 21 are then completely filled with dielectric material 23. Advantageously the dielectric material 23 is the same used for forming the dielectric layer 20. The heating layer is removed outside the openings 21 by CMP ("Chemical Mechanical Polishing") and the surface of the wafer

10 is planarized. The remaining portions of the heating layer form cup-shaped regions 22 that, in a top view, are visible as rings of conductive heating material immersed in the dielectric layer 20 and surrounding the dielectric material 23.

Next, as shown in the enlarged detail of Figure 8, a mold layer 27, for instance USG having a thickness of 20 nm, an adhesion layer 28, for instance Ti or Si with a thickness of 5 nm, and a first delimiting layer 29, for example nitride or another material that enables selective etching with respect to the adhesion layer 28, are deposited in sequence. The first delimiting layer 29 has a thickness of, for instance, 150 nm. Then, using a mask, one part of the first delimiting layer 29 is removed by dry etching to form a step which has a vertical side 30 that extends vertically on top of the dielectric material 23. The structure shown in Figure 8 is thus obtained.

Next (Figure 9), a sacrificial layer 31, for example TiN with a thickness of 30 nm, is deposited conformally. In particular, the sacrificial layer forms a vertical wall 31a that extends along the vertical side 30 of the first delimiting layer 29.

Next (Figure 10), the sacrificial layer 31 undergoes an etch back that results in removal of the horizontal portions of the sacrificial layer 31 and of part of the vertical wall 31a. By appropriately choosing the thickness of the first delimiting layer 29 and the thickness of the sacrificial layer 31, as well as the time and type of etching, it is possible to obtain the desired sublithographic width W1 for the bottom part of the remaining vertical wall 31a.

As shown in Figure 11, a second delimiting layer 35, of the same material as the first delimiting layer 29, for example nitride, with a thickness of 300 nm, is deposited. Next, the delimiting layers 29, 35 and the vertical wall 31a are thinned by chemical mechanical polishing (CMP). At the end, the remaining portions of the delimiting layers 29, 35 form a hard

mask, and the remaining portion of the vertical wall forms a sacrificial region 36.

5 Next (Figure 12), the sacrificial region 36 is removed. The adhesion layer 28 is isotropically etched, and the mold layer 27 is dry etched to form a slit 37 in the mold layer 27, the slit 37 having a width W_1 equal to the width of the sacrificial region 36.

10 Next (Figure 13), the delimiting layers 29, 35 are removed, and a chalcogenic layer 38, for example of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ with a thickness of 60 nm, is deposited conformally. The portion 38a of the chalcogenic layer 38 fills the slit 37 and forms, at the intersection with the cup-shaped region 22, a phase change
15 region similar to the phase change portion 4 of Figure 3. Then, on top of the chalcogenic layer 38, a barrier layer 39, for example of Ti/TiN, and a metal layer 40, for example of AlCu, are deposited. The structure of Figure 13 is thus obtained.

20 Next (Figure 14), the stack formed by the metal layer 40, barrier layer 39, chalcogenic layer 38, and adhesion layer 28 is defined using a same mask to form a bit line 41. Finally, a third dielectric layer 42 is deposited, planarized, for
25 example by CMP, and then opened above the base contacts 19b and above a portion (not shown) of the bit line 41. The openings thus formed are filled with tungsten to form top contacts 43 in order to prolong upwards the base contacts 19b. Then standard steps are performed for forming the connection
30 lines for connection to the base contacts 19b and to the bits lines 41, and the final structure of Figure 14 is thus obtained.

35 In practice, as shown in Figure 15, the intersection between the cup-shaped region 22 and the thin portion 38a of the chalcogenic layer 38 forms a contact area 45 which is approximately square and has sublithographic dimensions. This is due to the fact that both the cup-shaped region 22 and the

thin portion 38a have a width equal to the thickness of a deposited layer. In fact, the width of the cup-shaped region 22 is given by the thickness of the heating layer, and the width of the thin portions 38a is determined by the thickness of the sacrificial layer 31 along the vertical side 30. In greater detail, in the proximity of the contact area 45, the cup-shaped region 22 has a sublithographic dimension in a first direction (Y direction), and the thin portion 38a has a sublithographic dimension (width W1 of Figure 10) in a second direction (X direction) which is transverse to the first direction. Hereinafter, the term "sublithographic dimension" means a linear dimension smaller than the minimum dimension achievable with current optical (UV) lithographic techniques, and hence smaller than 100 nm, preferably 50-60 nm, down to approximately 5-20 nm.

In the process described above, it is necessary to deal with the issue of fixing the chalcogenic layer 38 exceeding the thin portion 38a which fills the slit 37. In fact, the chalcogenic layer 38 does not adhere tightly to the mold layer 27, which is made of USG or other dielectric material. Hence, the chalcogenic layer 38 can delaminate from the mold layer 27. In particular, the deposition of the chalcogenic layer 38 is followed by process steps that require heating and thermal stress, such as annealing, oxidation, barrier and metallic layer deposition. As is known, the risk of detachment of the chalcogenic layer 38 is particularly high during process steps which involve thermal stress. Thus, the intermediate adhesion layer 28 of a suitable adhering material, such as Ti or Si, must be provided. However, also this solution is not fully satisfactory. On the one hand, the adhesion layer 28 must extend by a quite large amount over the mold layer 27 to provide enough adhesion surface for the chalcogenic layer 38. Therefore, also the bit line 41, which is made on the chalcogenic layer 38 and on the adhesion layer 28 is rather wide. On the other hand, the stack comprising the adhesion layer 28, the chalcogenic layer 38, the barrier layer 39 and the metal layer 40 is some hundreds nanometers high. However,

the adhesion layer 28 and the chalcogenic layer 38 together are normally at least 60-100 nm high. In other words, a substantial part of the height of the stack is required at the sole purpose of preventing detachment of the chalcogenide.

5

On the contrary, a process that allows reducing the overall dimensions of the phase change memory cell and a phase change memory cell having reduced overall dimensions are desirable.

10 Moreover, forming the thin portion 38a of the chalcogenic layer 38 entails numerous steps and is somewhat complex.

Consequently, it is desirable to have a simpler alternative process.

15

The aim of the present invention is to improve and simplify the process described in patent application 01128461.9, with particular regard to the issue of the poor adhesion between the chalcogenic material and the non-conductive molding layer.

20

According to the present invention there are provided a self-aligned process for manufacturing a phase change memory cell and a phase change memory cell thereby manufactured, as defined in claims 1 and 10, respectively.

25

For a better understanding of the present invention, some preferred embodiment thereof are now described, purely by way of non-limiting example, with reference to the attached drawings, in which:

- 30 - Figure 1 shows the current versus voltage characteristic of a phase change material;
- Figure 2 shows the temperature versus current plot of a phase change material;
- Figure 3 shows the basic structure of a PCM memory element;
- 35 - Figure 4 shows a cross section of a wafer of semiconductor material in a manufacturing step of the cell of Figure 3, according to the aforementioned patent application;

- Figure 5 shows the layout of some masks used for forming the structure of Figure 4;
- Figure 6 is a cross-section taken along line VI-VI of Figure 5;
- 5 - Figures 7-14 are cross-section of the structure of the above mentioned patent application, in successive manufacture steps;
- Figure 15 is a top plan view, with parts removed and at an enlarged scale, of a detail of Figure 14;
- Figures 16a and 16b are top plan views, with parts removed, of a detail of Figure 14, under two different manufacture conditions;
- 10 - Figure 17 shows the layout of some masks used for forming the structure of Figure 7, according to the invention;
- Figure 18 is a cross-section similar to Figure 8, in a manufacture step according to a first embodiment of the invention;
- 15 - Figure 19 shows the layout of some masks used for forming the structure of Figure 18;
- Figures 20 and 21 are cross-sections, similar to Figure 18, in successive manufacture steps according to the first embodiment of the invention;
- 20 - Figure 22 is a top plan view of the structure of Figure 21;
- Figures 23-26 are cross-sections, similar to Figure 21, in subsequent manufacture steps;
- 25 - Figure 27 shows the layout of same masks used for forming the structure of Figure 26;
- Figure 28 is a cross-section, similar to Figure 14, in a final manufacture step according to the first embodiment of the invention;
- 30 - Figures 29-32 are cross-sections, similar to Figure 8, in manufacture steps according to a second embodiment of the invention;
- Figures 33-35 are cross-sections, similar to Figure 32, in manufacture steps according to a third embodiment of the invention;
- 35 - Figure 36 is a cross-section, similar to Figure 14, in a final manufacture step according to the third embodiment of the invention.

In the following description, parts that are the same as those previously described with reference to Figures 4-14 are designated by the same reference numbers.

5 The process according to the present invention comprises initial steps equal to those described in patent application 01128461.9 illustrated above, up to deposition of the second dielectric layer 20 (Figure 7). Next, also here the openings
10 21 and the cup-shaped regions 22 are formed. However, as shown in Figure 17, for the definition of the openings 21, a heater mask D is used which has rectangular windows (the term "rectangular" also comprising the particular case of a square shape). Consequently, the openings 21 have a substantially
15 rectangular shape. Then the heating layer, for example of TiSiN, TiAlN or TiSiC, with a thickness of 10-50 nm, preferably 20 nm, is deposited. The heating layer coats the walls and bottom of the openings 21 conformally. The openings
20 21 are then filled with dielectric material 23 and the heating layer is removed outside the openings 21, e.g. by CMP, to form the cup-shaped regions 22. Consequently, in top plan view, the cup-like regions 22 here define an ideally rectangular shape, possibly with rounded edges (on account of the lithographic limits), or at the most an ovalized shape, with the longer
25 side, or main direction, parallel to the X direction (Figure 22).

Then (Figure 18), a stop layer 48, for example of nitride deposited by PECVD (Plasma Enhanced Chemical Vapor Deposition)
30 with a thickness of 40 nm, and a mold layer 49, for example of USG deposited by PECVD or SACVD (Sub-Atmospheric Chemical Vapor Deposition) with a thickness of 50-70 nm, are deposited in sequence, so as to form a minitrench stack 50.

35 Next, using a minitrench mask, designated by E in Figure 19, the mold layer 49 and the stop layer 48 are etched. As shown in Figure 19, the minitrench mask E has a rectangular window that extends between two adjacent cells 5 in the Y direction

(perpendicular to the alignment direction of the base and emitter regions 14, 15 of each memory cell 5, Figure 7).

5 With subsequent etching, part of the minitrench stack 50 (layers 48 and 49) is removed, so as to form an opening 51 having a rectangular shape, corresponding to that of the minitrench mask E. The width of the opening 51 in the X direction is, for example, 160 nm. The opening 51 uncovers part of the dielectric material 23 of the two adjacent cells 5 and crosses each cup-shaped region 22 only once, as can be clearly seen from the superposition of the heater mask D and minitrench mask E in Figure 19.

15 Next, Figure 20, a spacer layer 55, for example an oxide layer, is deposited (in particular, TEOS with a thickness of 50 nm). The spacer layer 55 covers the mold layer 49, as well as the walls and bottom of the opening 51.

20 Then, Figure 21, the spacer layer 55 is anisotropically etched by etching back until the horizontal portions thereof are removed, according to the well known spacer formation technique. The spacer layer 55 is then completely removed above the mold layer 49 and is partially removed from the bottom of the opening 51 to form a spacer region 55a which extends along the vertical sides of the opening 51 (along the perimeter of a rectangle or of an oval) and delimits a slit 56, the base whereof forms a rectangular strip 57 having a sublithographic width W2 (in the X direction) of approximately 60 nm. Figure 22 is a top plan view of the structure thus obtained, and highlights how the strip 57 uncovers only one portion of the cup-shaped region 22 of each cell 5, shown with dashed line in the figure. The uncovered portion of each cup-shaped region 22 forms a contact area 58, as will be explained hereinafter.

35 Next, Figure 23, the chalcogenic layer 38 is deposited (also in the present case, for instance, of $\text{Ge}_2\text{Sb}_2\text{Te}_5$ with a thickness of 60 nm). The chalcogenic layer 38 is in direct

contact with the mold layer 49 and fills the slit 56 with a thin portion 38a. In particular, the thin portion 38a of the chalcogenic layer 38 deposits on the strip 57, contacting the cup-shaped regions 22 at the contact areas 58. The inclined wall formed by the spacer region 55a favors filling of the slit 56, so preventing problems linked to a poor aspect ratio of the opening 51.

Then, Figure 24, a thick portion 38b of the chalcogenic layer 38, exceeding the slit 56 is removed, preferably by CMP ("Chemical Mechanical Polishing"). The CMP process is terminated on reaching the mold layer 49: accordingly, the thin portion 38a, which is housed in the slit 56, is left. Moreover, the thin portion 38a is self-aligned to the mold layer 49. Although the chalcogenic layer 38 poorly adheres to the mold layer 49, detachment does not occur during this step, which lacks thermal stresses. As an alternative, the thick portion 38b may be removed by etch-back, using the mold layer 49 as a stop layer.

The barrier layer 39, preferably of Ti/TiN, the metal layer 40, of AlCu, and a cap layer 44 of Ti or other suitable material are deposited in succession, to form a conductive stack 41 covering the mold layer 49 and the thin portion 38a (Figure 25). The barrier layer 39 perfectly adheres to the mold layer 49 and seals the thin portion 38a inside the slit 56, thereby preventing detachment during later steps of manufacturing.

Next, the conductive stack 41 is defined using a stack mask F (Figure 27) for forming bit lines 41' (Figure 26).

The process continues with the steps described previously, which comprise deposition and CMP planarization of the third dielectric layer 42, opening of the third dielectric layer 42 above the base contacts 19b and above a portion (not shown) of the bit lines 41', formation of the top contacts 43, and formation of connection lines for connection to the base

contacts 19b and to the bit lines 41', so as to obtain the final structure shown in Figure 28.

5 The advantages of the process and structure described herein are illustrated hereinafter. First, the problems caused by the poor adhesion between chalcogenic and dielectric materials are completely overcome. In fact, since no thermal stress is involved in removing the thick portion 38b of the chalcogenide layer 38, the probability of detachment (in particular, of the
10 thin portion 38a) is very low. In the next process step, the remaining thin portion 38a is sealed inside the slit 57.

15 It is also clear that the phase change memory manufactured according to the present invention has a compact structure and, especially, reduced height. The above described embodiment is particularly advantageous, since both the thick portion 38b of the chalcogenic layer 38 and the adhesion layer 28 are eliminated.

20 Moreover, the need for the adhesion layer is overcome, thereby simplifying the process.

Also the sequence of steps required for forming the thin portion 38a is simplified; in particular, self-aligned process
25 steps are advantageously exploited. Furthermore the opening 51 is correctly filled, thanks to the inclination of the spacer region 55a, as mentioned previously.

30 According to a second embodiment of the invention, which is illustrated in figures 29-31, after forming and filling the cup-shaped regions 22, the stop layer 48, the mold layer 49 and an adhesion layer 60 are deposited, so as to form a minitrench stack 66. Then (figure 30), the minitrench stack 66 is etched using the minitrench mask E illustrated in figure 19
35 and an opening 67 is formed which extends vertically through the adhesion layer 60, the mold layer 49 and the stop layer 48, thereby exposing portions of the cup-shaped region 22. Moreover, the opening 67 has a rectangular shape,

corresponding to that of the minitrench mask E. The width of the opening 67 in the X direction is, for example, 160 nm. The opening 51 uncovers part of the dielectric material 23 of the two adjacent cells 5 and crosses each cup-shaped region 22 only once, as can be clearly seen from the superposition of the heater mask D and minitrench mask E in Figure 19.

Then, a spacer layer 70 (illustrated by a dotted line in figure 31) is deposited and anisotropically etched to form a spacer region 70a on the vertical sides of the opening 67. The spacer region 70a has inclined walls and delimits a slit 71, the base whereof forms a rectangular strip 72 having the sublithographic width W2 (in the X direction) of approximately 60 nm. The uncovered portion of each cup-shaped region 22 forms a contact area 75.

Thereafter, the chalcogenic layer 38 is deposited on the adhesion layer 60 and fills the slit 71 with the thin portion 38a (figure 32). Both the thick portion 38b of the chalcogenic layer 38 exceeding the slit 71 and the adhesion layer 60 are then completely removed by CMP process, which is terminated when the mold layer 49 is exposed. The structure already illustrated in figure 24 is thus obtained.

The steps already described with reference to figures 25-27 are then carried out, so as to obtain the final structure shown in Figure 28, namely deposition and shaping of the conductive stack 41 and bit lines 41', deposition and planarization of the third dielectric layer 42, opening of the third dielectric layer 42 above the base contacts 19b and above a portion (not shown) of the bit lines 41', formation of the top contacts 43, and formation of connection lines for connection to the base contacts 19b and to the bit lines 41'.

In this case, one deposition step is added, for forming the adhesion layer 60, but the probability of detachment of the chalcogenic layer 38 is substantially eliminated.

A third embodiment of the invention is illustrated in Figures 33-36. Initially, all the same process steps as previously described are carried out to obtain the structure shown in figure 32. In particular, the chalcogenic layer 38 has been
5 deposited on the minitrench stack 66 and the thin portion 38a fills the slit 71; moreover, the minitrench stack 66 comprises the adhesion layer 60. The thick portion 38b of the chalcogenic layer is then removed by CMP, Figure 33. In this case, the adhesion layer 60 is used as a stop layer during the
10 CMP process and is not removed. Hence, the thin portion 38a, which is housed in the slit 71, is self-aligned to the adhesion layer 60. Of course, the adhesion layer 60 also delimits the thin portion 38a.

15 The barrier layer 39, the metal layer 40, and the cap layer 44 are deposited in succession, to form the conductive stack 41 covering the adhesion layer 60 and the thin portion 38a (Figure 34). The barrier layer 39 perfectly adheres to the adhesion layer 60 and seals the thin portion 38a inside the
20 slit 71 thereby preventing detachment during later steps of manufacturing.

Next, the conductive stack 41 is defined using the stack mask F for forming bit lines 41' (Figure 35). During this step,
25 also the adhesion layer is etched, so that only residual portions 60a thereof are left between the mold layer 49 and the barrier layer 39.

Thereafter, the third dielectric layer 42 is deposited,
30 planarized, and then opened above the base contacts 19b and above a portion (not shown) of the bit lines 41', the top contacts 43 and connection lines for connection to the base contacts 19b and to the bit lines 41' are formed. The structure illustrated in Figure 36 is thus obtained.

35 Finally, it is clear that numerous modifications and variations may be made to the process and to the memory cell described and illustrated herein, all falling within the scope

of the invention, as defined in the attached claims. In particular, a slit having sublithographic width and inclined walls can be provided in any suitable manner, other than the above described one. Moreover, although inclined walls
5 advantageously favor filling the slit, also slits with vertical walls can be used.

CLAIMS

1. A process for manufacturing a phase change memory cell, comprising the steps of:
5 forming a resistive element (22);
forming a delimiting structure (48, 49, 55a; 48, 49, 60, 70a) having an aperture (56; 71) over said resistive element (22);
forming a memory portion (38a) of a phase change material in said aperture, said resistive element (22) and said memory
10 portion (38a) being in direct electrical contact and defining a contact area (58) of sublithographic extension;
wherein said step of forming a memory portion (38a) comprises filling said aperture (56; 71) with said phase change material and removing from said delimiting structure (48, 49, 55a; 48,
15 49, 60, 70a) an exceeding portion (38b) of said phase change material exceeding said aperture (56; 71).
2. A process according to claim 1, wherein said step of
20 removing is followed by the step of sealing said memory portion (38a) inside said aperture.
3. A process according to claim 2, wherein said step of
25 sealing comprises depositing a sealing structure (41) directly on said delimiting structure (48, 49, 55a; 48, 49, 60, 70a).
4. A process according to any one of the foregoing claims,
wherein said step of filling comprises depositing a memory
layer (38) on said delimiting structure (48, 49, 55a; 48, 49,
60, 70a).
- 30 5. A process according to claim 4, wherein said step of forming said delimiting structure (48, 49, 55a; 48, 49, 60, 70a) comprises depositing at least a dielectric layer (49).
- 35 6. A process according to claim 5, wherein said step of filling comprises depositing said memory layer (38) directly on said dielectric layer (49).

7. A process according to claim 5, wherein, before said step of filling, an adhesion layer (60) is deposited on said dielectric layer (49).

5 8. A process according to claim 7, wherein said step of removing comprises completely removing said adhesion layer (60).

9. A process according to any one of the foregoing claims,
10 wherein said resistive element (22) include a first thin portion having a first sublithographic dimension in a first direction (Y) and said memory portion (38a) has a second sublithographic dimension in a second direction (X) transverse to said first direction; said contact area (58) of
15 sublithographic extension having substantially said first sublithographic dimension in said first direction (Y) and said second sublithographic dimension in said second direction (X).

10. A phase change memory cell (5), comprising:
20 a resistive element (22);
a delimiting structure (48, 49, 55a; 48, 49, 60a, 70a), having an aperture (56; 71) over said resistive element (22);
a memory portion (38a) of a phase change material, housed in said aperture, said resistive element (22) and said memory
25 portion (38a) being in direct electrical contact and defining a contact area (58) of sublithographic extension;
wherein said memory portion (38a) is sealed inside said aperture (56; 71) by a sealing structure (41') directly lying on said delimiting structure (48, 49, 55a; 48, 49, 60a, 70a).
30

11. A phase change memory cell according to claim 10, wherein said delimiting structure (48, 49, 55a; 48, 49, 60a, 70a) comprises at least a dielectric layer (49).

35 12. A phase change memory cell according to claim 11, wherein said sealing structure (41') lies directly on said dielectric layer (49).

13. A phase change memory cell according to claim 11, wherein said delimiting structure (48, 49, 60a, 70a) comprises adhesion portions (60a) interposed between said dielectric layer (49) and said sealing structure (41').

5

14. A phase change memory cell according to any one of claims 10-13, wherein said memory portion (38a) is aligned with said delimiting structure (48, 49, 55a; 48, 49, 60a, 70a).

10 15. A phase change memory cell according to any one of the claims 10-14, wherein said sealing structure (41') comprises a stack of conducting layers (39, 40, 44).

15 16. A phase change memory cell according to any one of the claims 10-15, wherein said resistive element (22) include a first thin portion having a first sublithographic dimension in a first direction (Y) and said memory portion (38a) has a second sublithographic dimension in a second direction (X) transverse to said first direction; said contact area (58) of
20 sublithographic extension having substantially said first sublithographic dimension in said first direction (Y) and said second sublithographic dimension in said second direction (X).

25 17. The memory cell according to any one of claims 10 to 16, wherein said memory portion (38a) has a substantially elongated shape with a main dimension extending parallel to said first direction (Y).

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ABSTRACT

A process for manufacturing a phase change memory cell, comprising the steps of: forming a resistive element (22);
5 forming a delimiting structure (48, 49, 55a) having an aperture (56) over the resistive element (22); forming a memory portion (38a) of a phase change material in the aperture, the resistive element (22) and the memory portion (38a) being in direct electrical contact and defining a
10 contact area (58) of sublithographic extension. The step of forming a memory portion (38a) further includes filling the aperture (56) with the phase change material and removing from the delimiting structure (48, 49, 55a) an exceeding portion (38b) of the phase change material exceeding the aperture
15 (56).

Figure 28

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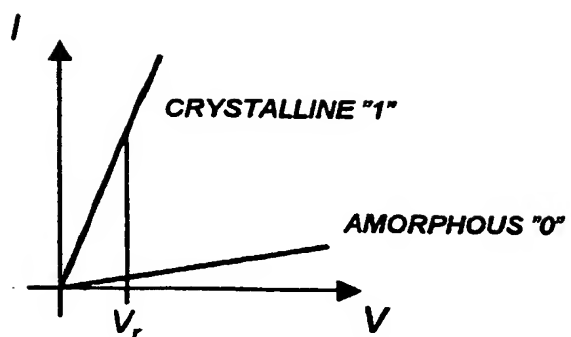


Fig. 1

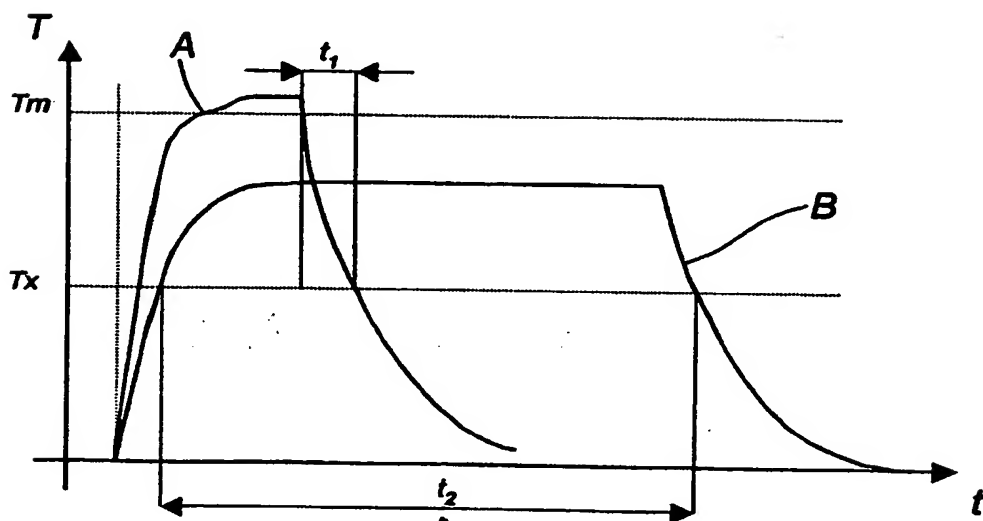


Fig. 2

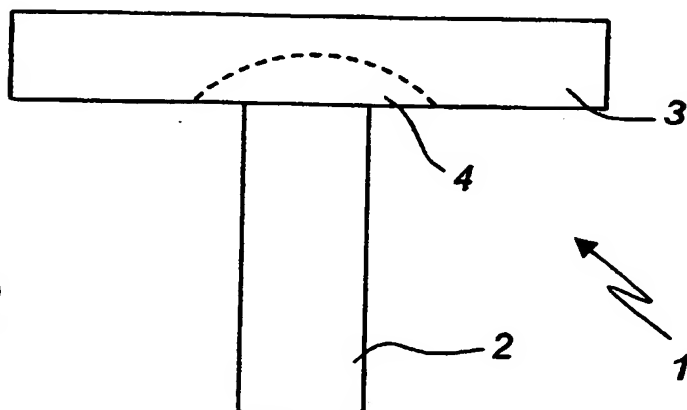
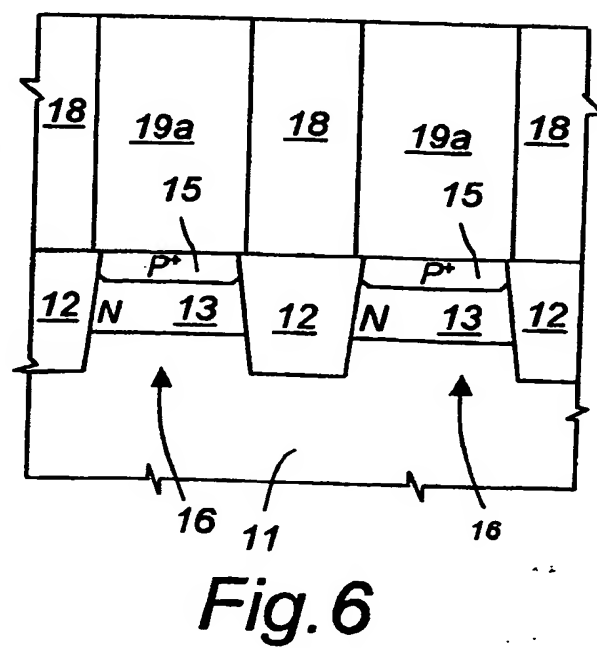
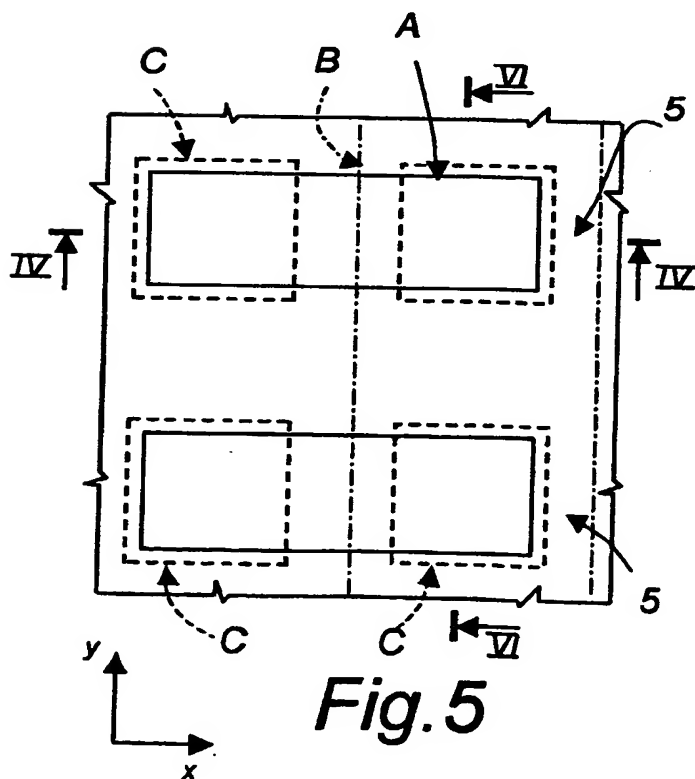
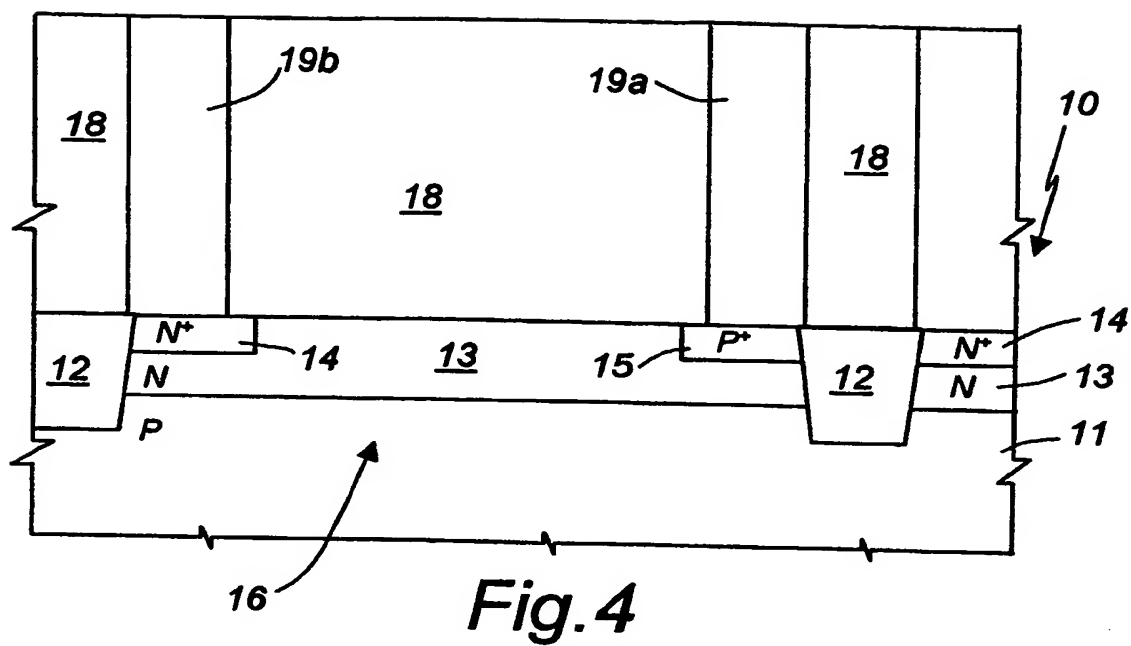


Fig. 3



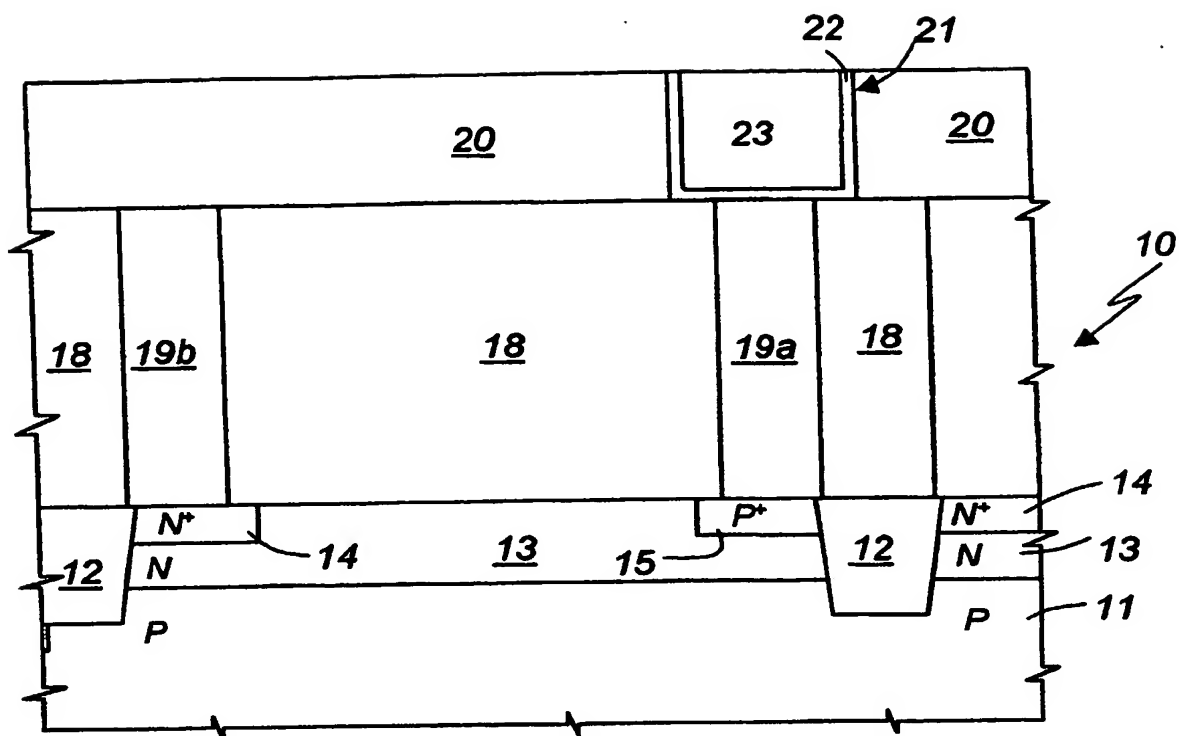


Fig. 7

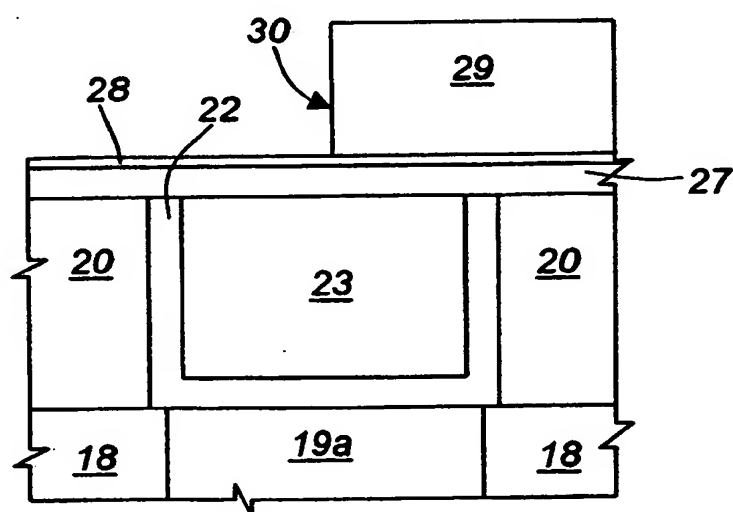


Fig. 8

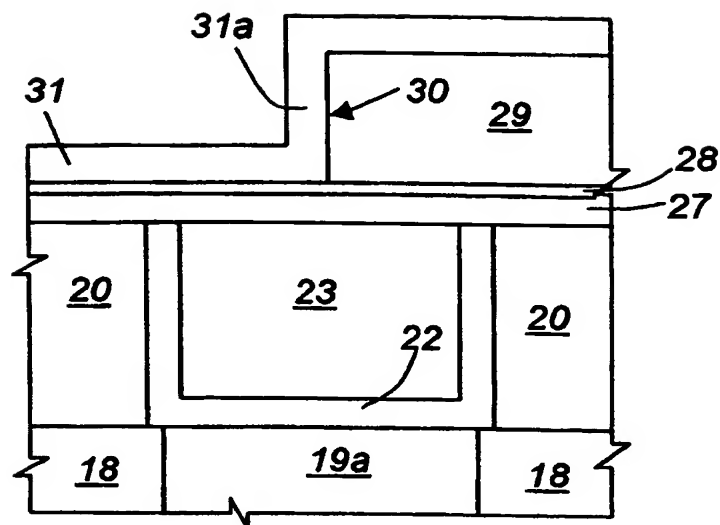


Fig. 9

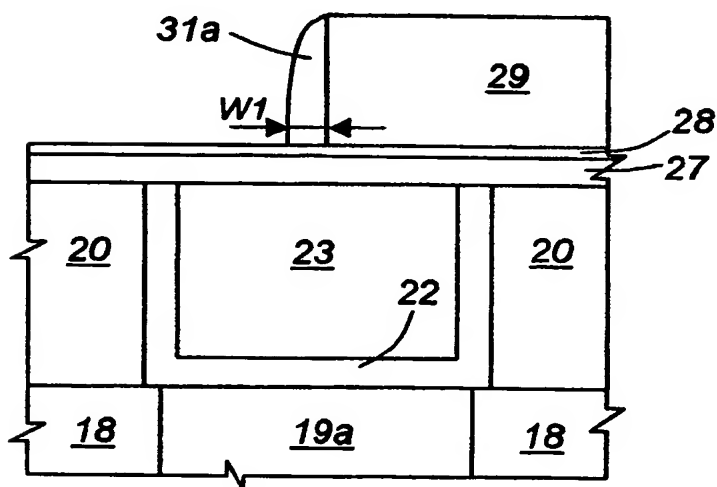


Fig. 10

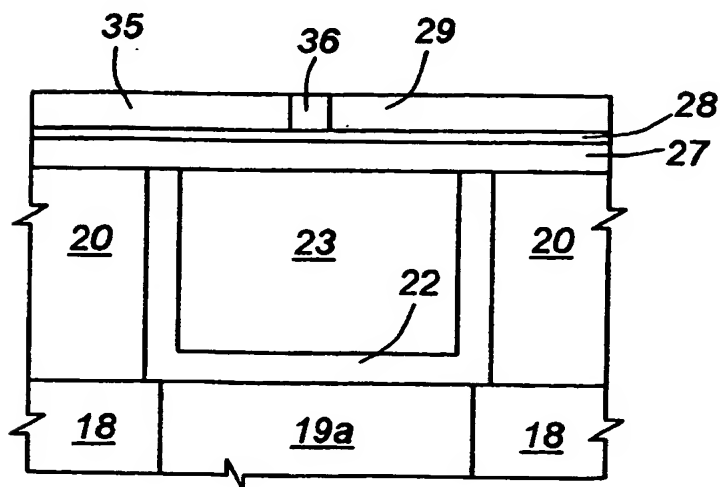


Fig. 11

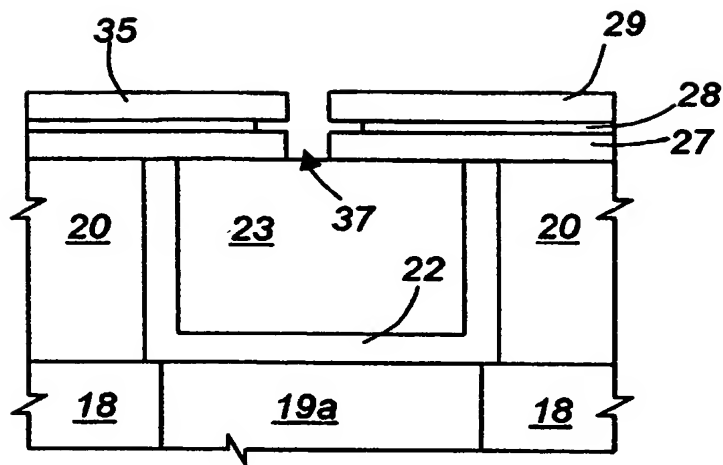


Fig. 12

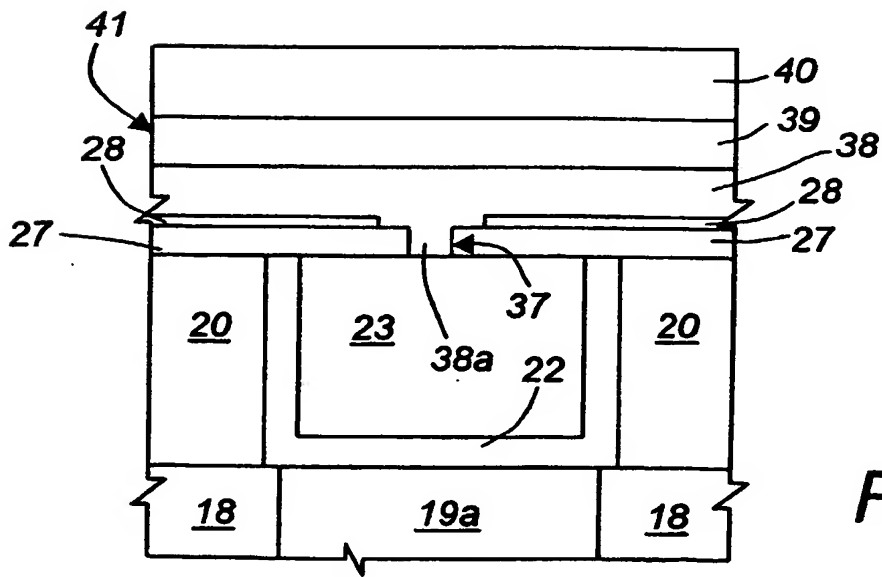
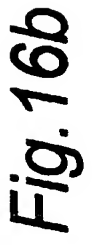
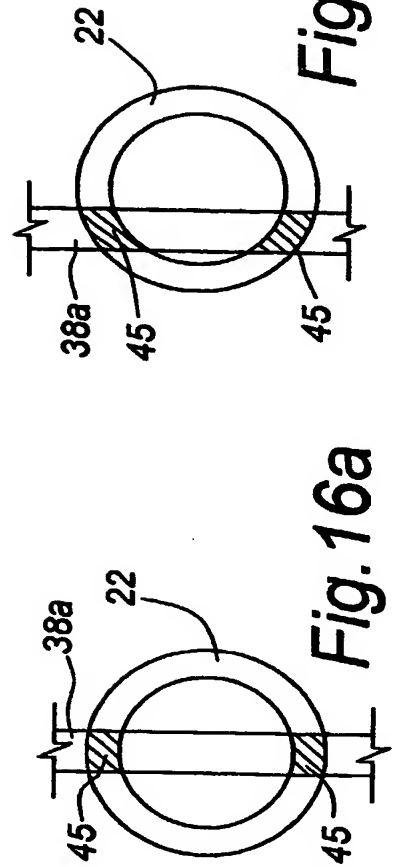
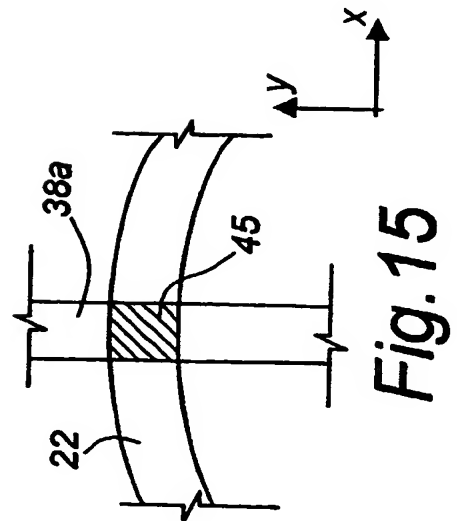
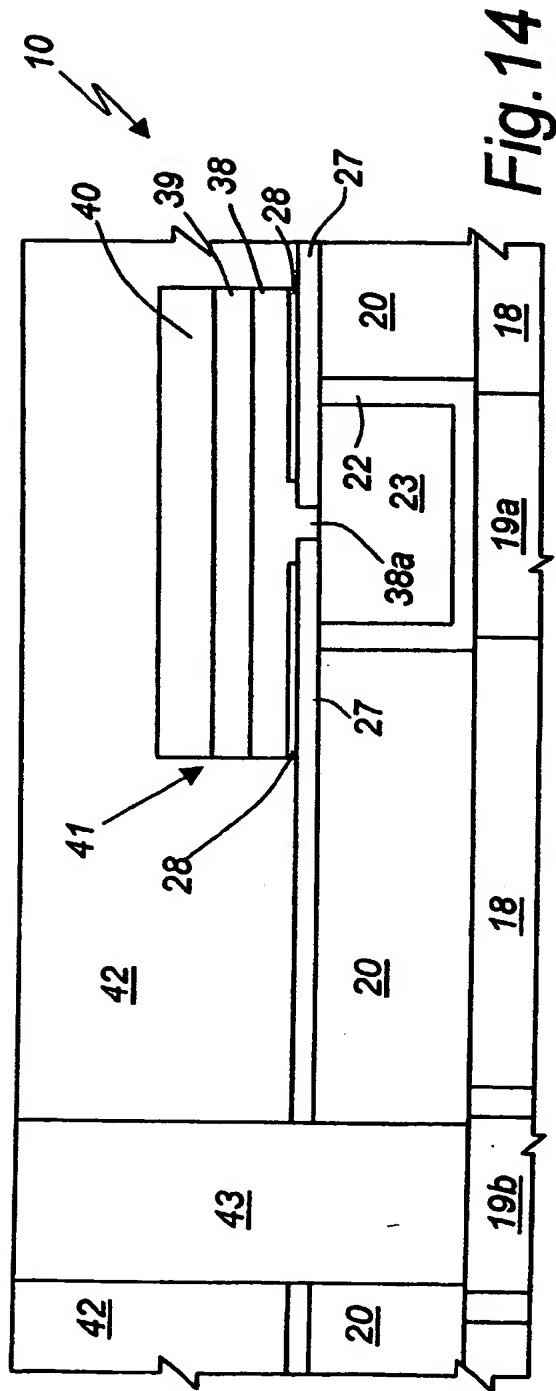
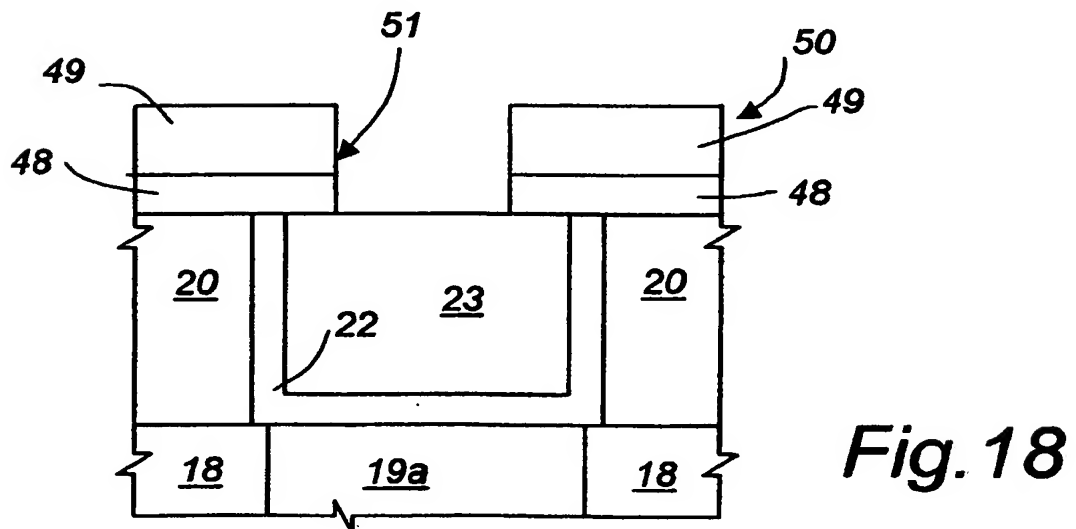
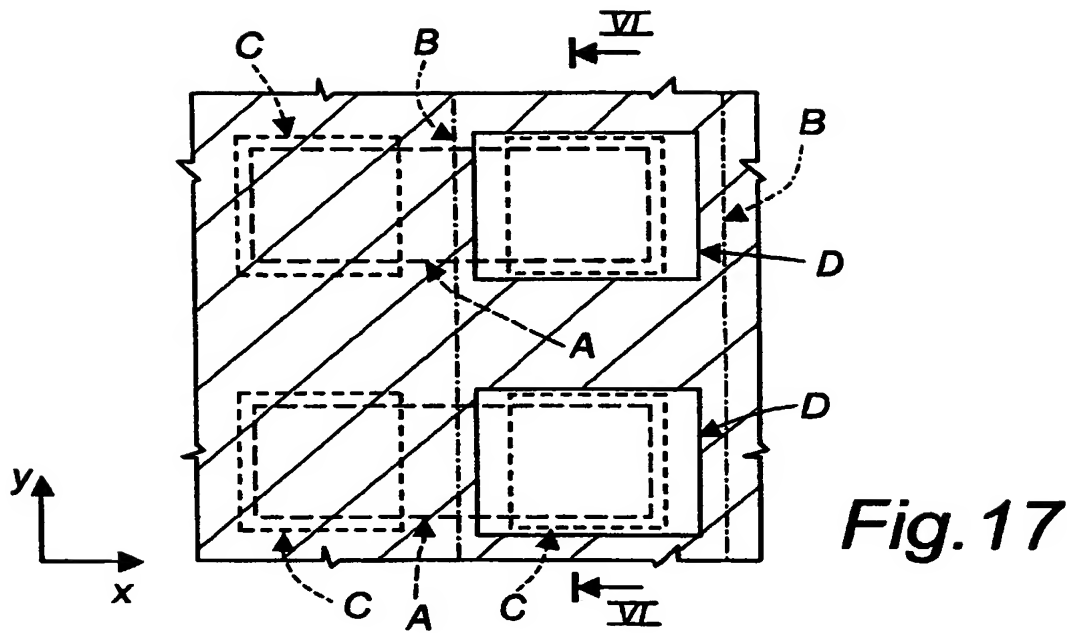


Fig. 13





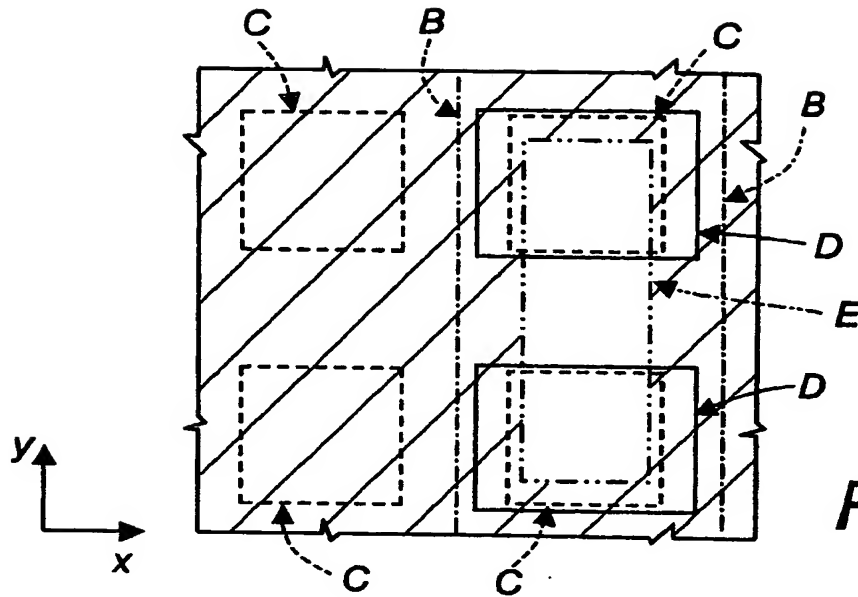


Fig. 19

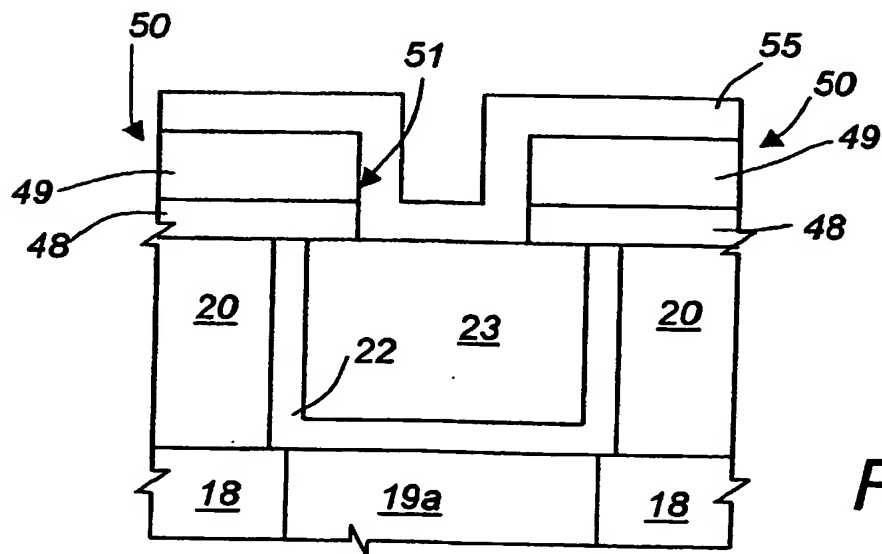


Fig. 20

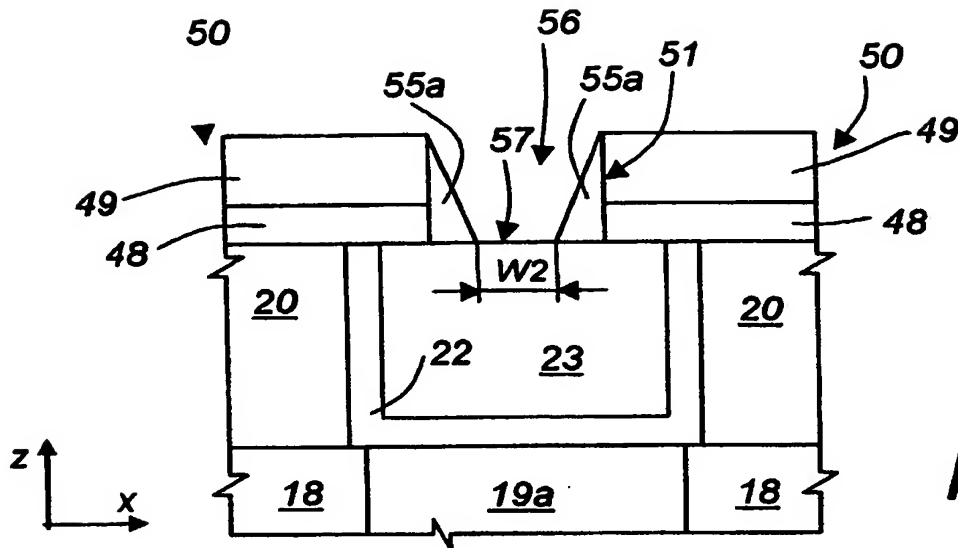


Fig. 21

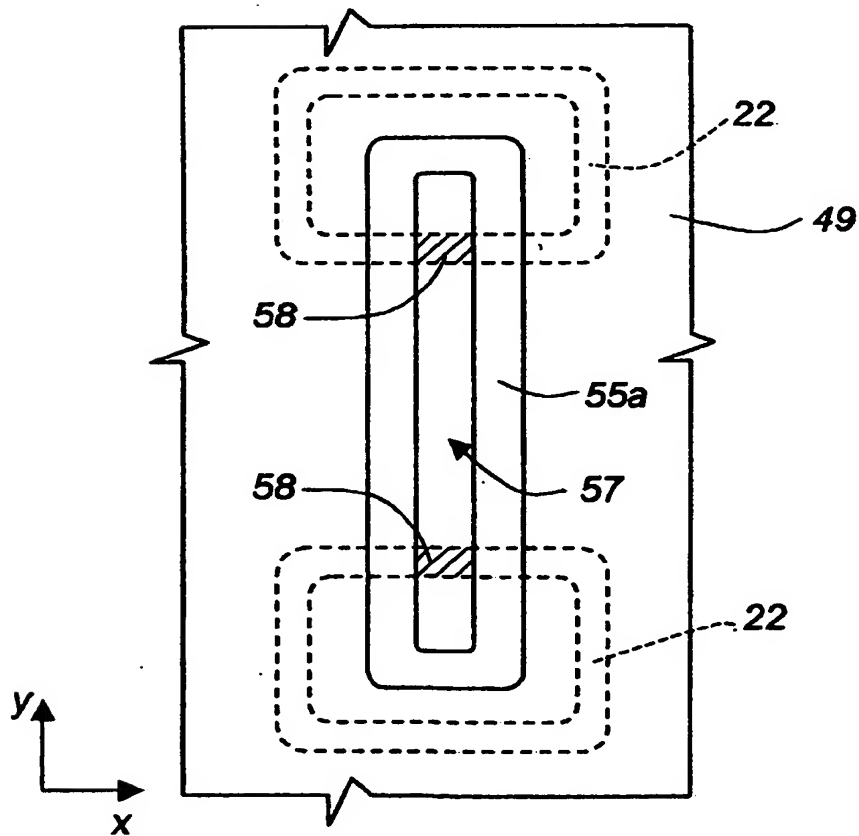
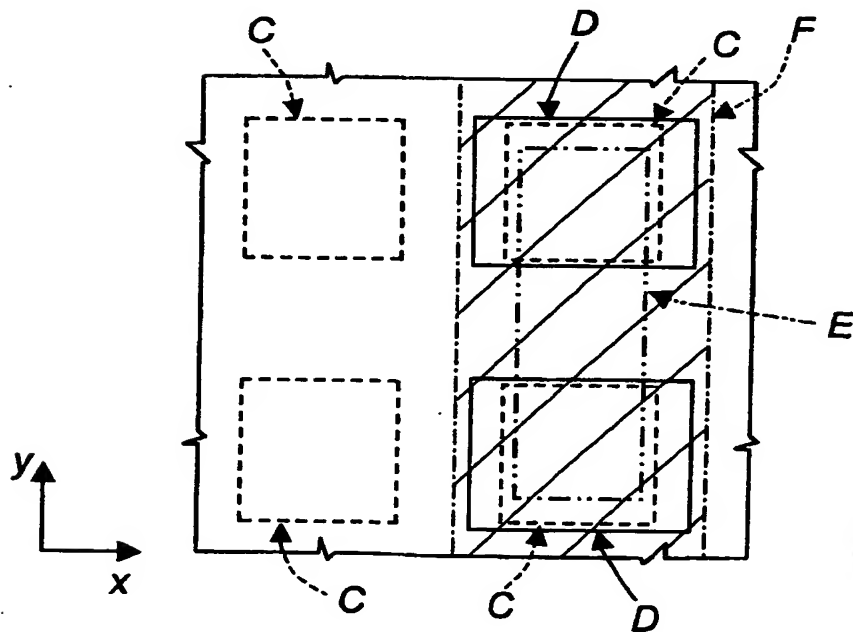
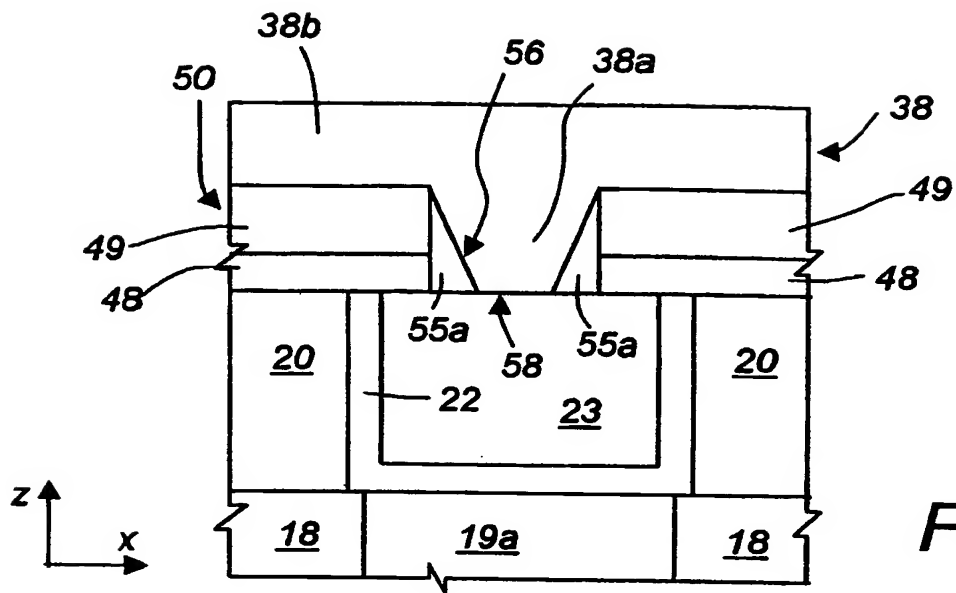


Fig. 22



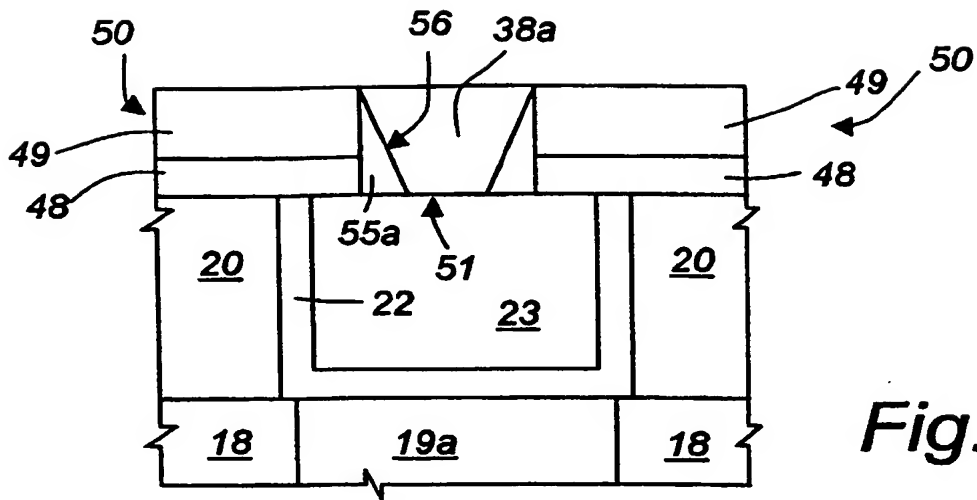


Fig. 24

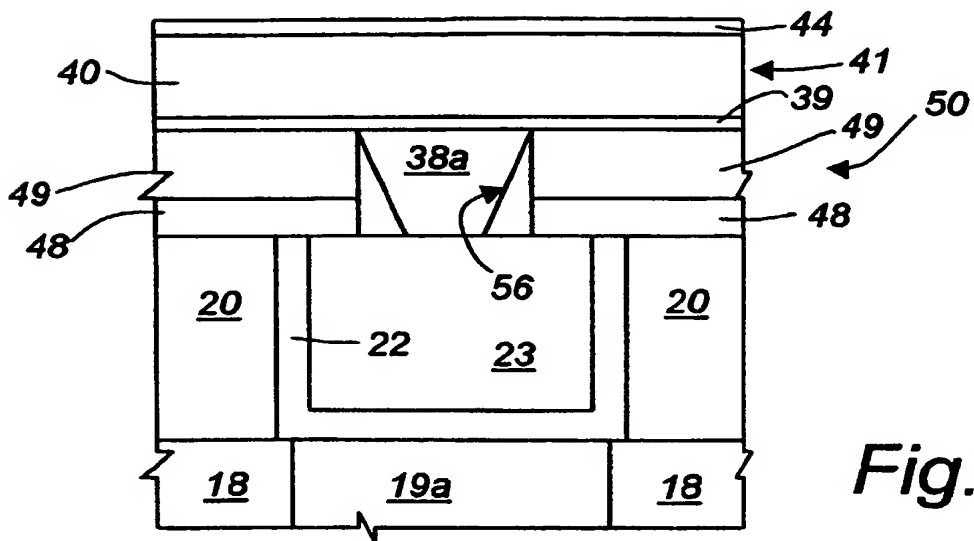


Fig. 25

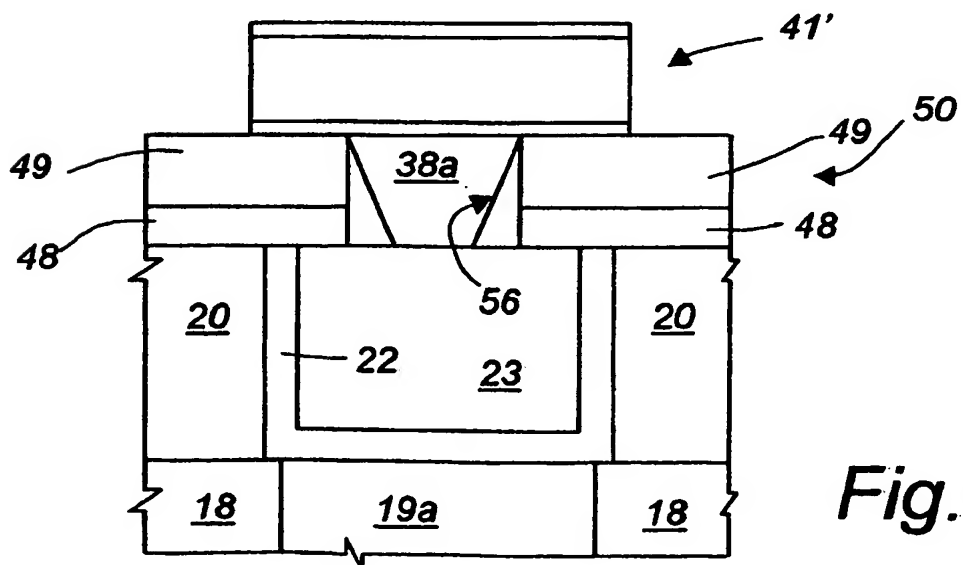
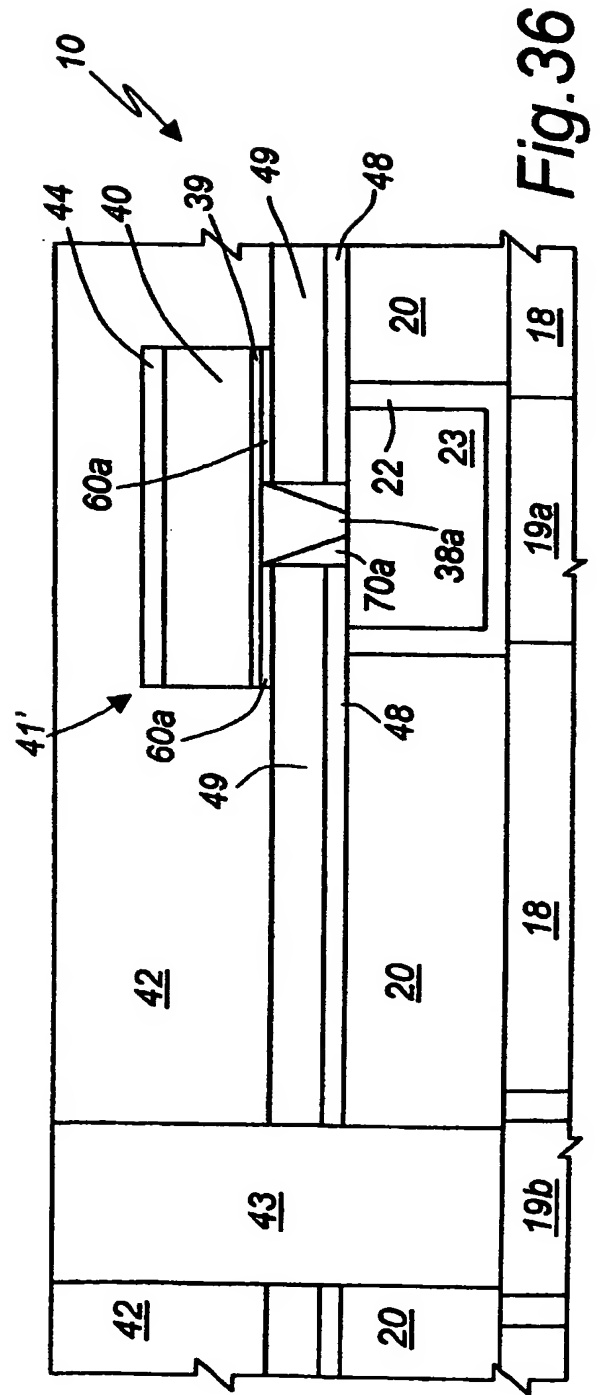
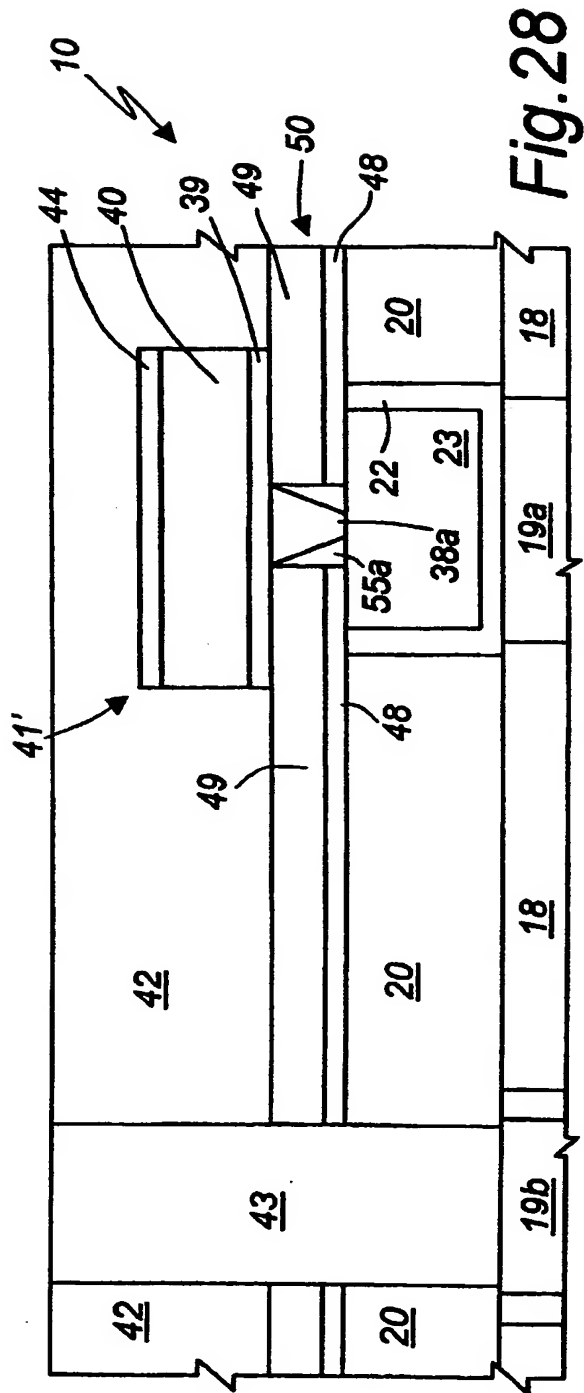


Fig. 26



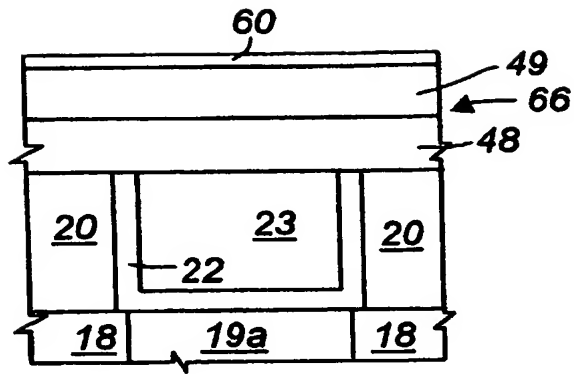


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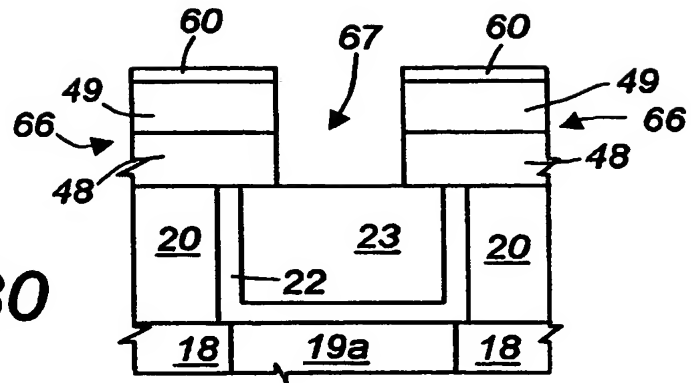


Fig. 30

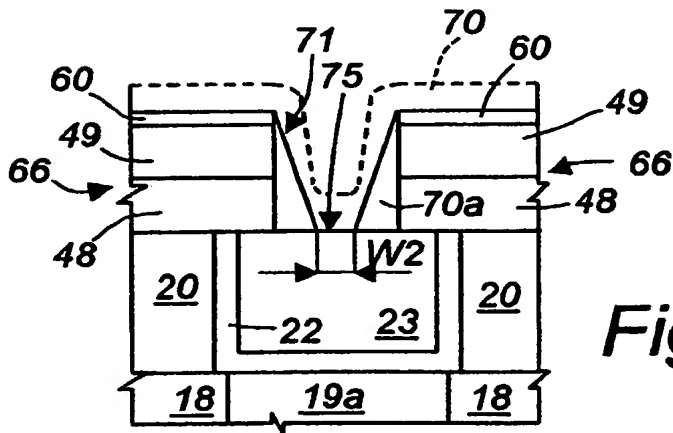


Fig. 31

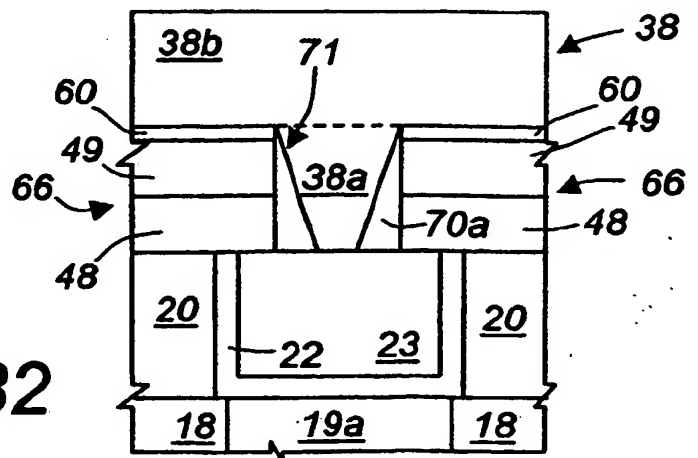


Fig. 32

